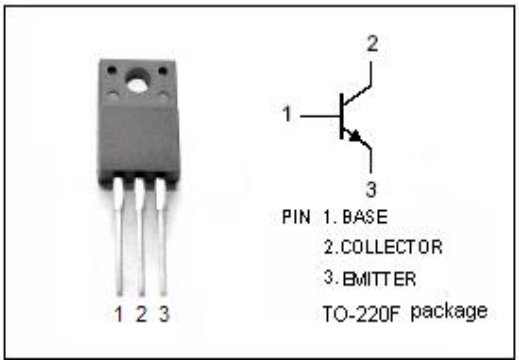
isc Silicon NPN Power Transistor — 2SD2021

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 150V (Min)
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

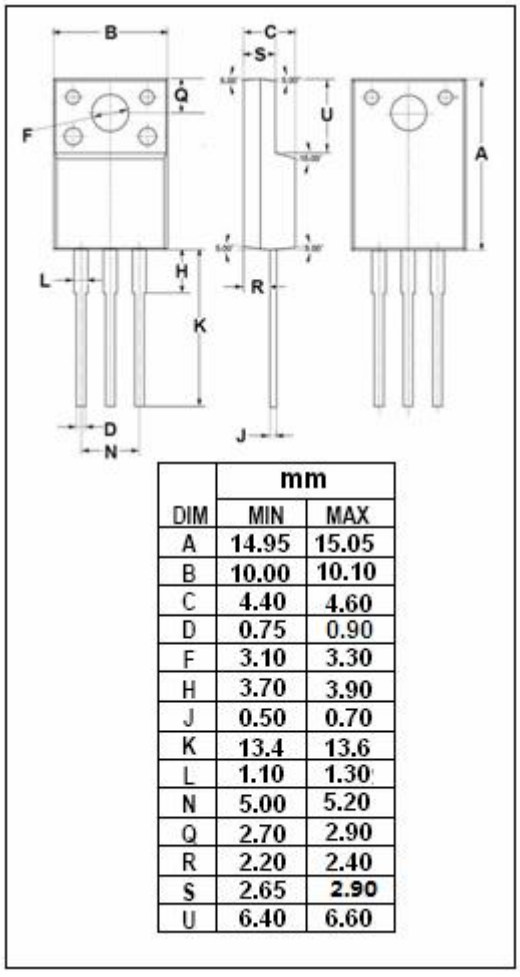


APPLICATIONS

- Designed for low frequency power amplifier TV vertical deflection output applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	2	A
I_{CM}	Collector Current-Peak	5	A
P_C	Collector Power Dissipation @ T_a=25℃	2	W
	Collector Power Dissipation @ T_C=25℃	30	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-45~150	℃



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 30mA; R_{BE}= ∞	150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 5mA; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.5A; I_B= 0.05A			3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 50mA ; V_{CE}= 5V			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CE}= 150V; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			10	μA
h_{FE-1}	DC Current Gain	I_C= 50mA; V_{CE}= 5V	100		320	
h_{FE-2}	DC Current Gain	I_C= 1A; V_{CE}= 5V	60			
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 100V; f_{test}= 1.0MHz		20		pF